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(54) Title: VAN DER WAALS CAPACITOR AND QUBIT USING SAME

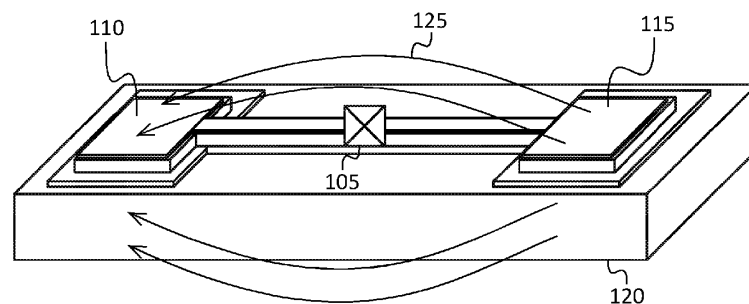


FIG. 1

(57) Abstract: A van der Waals capacitor and a qubit constructed with such a capacitor. In some embodiments, the capacitor includes a first conductive layer; an insulating layer, on the first conductive layer; and a second conductive layer on the insulating layer. The first conductive layer may be composed of one or more layers of a first van der Waals material, the insulating layer may be composed of one or more layers of a second van der Waals material, and the second conductive layer may be composed of one or more layers of a third van der Waals material.

[Continued on next page]

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